

ABSTRACT OF THE DISCLOSURE

A hermetically coated device includes an integrated semiconductor circuit die, a first layer comprising an inorganic material, the first layer
5 enveloping the integrated semiconductor circuit die, a second layer, the second layer enveloping the integrated semiconductor circuit die. Formation of such device includes steps of providing an integrated semiconductor circuit die, applying a first layer comprising an
10 inorganic material, the first layer enveloping the integrated semiconductor circuit die, and applying a second layer, the second layer enveloping the integrated semiconductor circuit die.

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